High Voltage Switching Diode, 250 V

BAS21TMR6

The BAS21TMR6T1G device houses three high−voltage switching diodes in a SC−74 surface mount package. This device is ideal for low−power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	250	Vdc
Forward Current	I_F	200	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	625	mAdc

THERMAL CHARACTERISTICS

| Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board (Note 1) T_A = 25°C Derate above 25°C	P_D	311 2.5	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	402	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	347 2.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	360	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. FR−4 @ 10 mm², 2 oz copper traces
2. FR−4 @ 25 mm², 2 oz copper traces
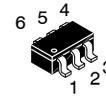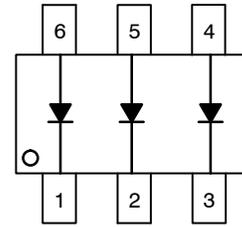
SC−74
CASE 318F

MARKING DIAGRAM
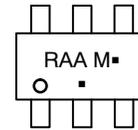
RAA = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device	Package	Shipping†
BAS21TMR6T1G	SC−74 (Pb−Free)	3000 / Tape & Reel
NSVBAS21TMR6T1G	SC−74 (Pb−Free)	3000 / Tape & Reel
NSVBAS21TMR6T2G	SC−74 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current (V_R = 200 Vdc) (V_R = 200 Vdc, T_J = 150°C)	I_R	– –	0.1 100	μAdc
Reverse Breakdown Voltage (I_{BR} = 100 μAdc)	$V_{(BR)}$	250	–	Vdc
Forward Voltage (I_F = 100 mAdc) (I_F = 200 mAdc)	V_F	– –	1.0 1.25	Vdc
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	–	5.0	pF
Reverse Recovery Time (I_F = I_R = 30 mAdc, $I_{R(REC)}$ = 3.0 mAdc, R_L = 100)	t_{rr}	–	50	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
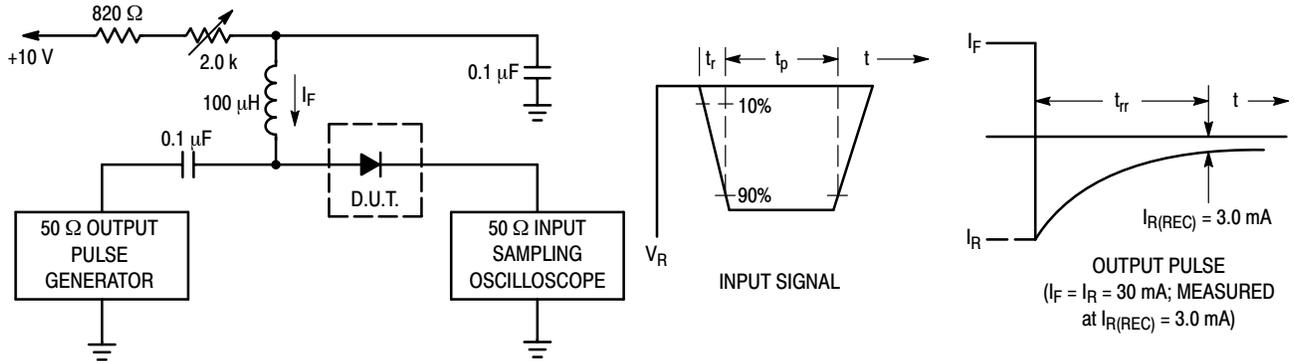
Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
      2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
      3. t_p » t_{rr}

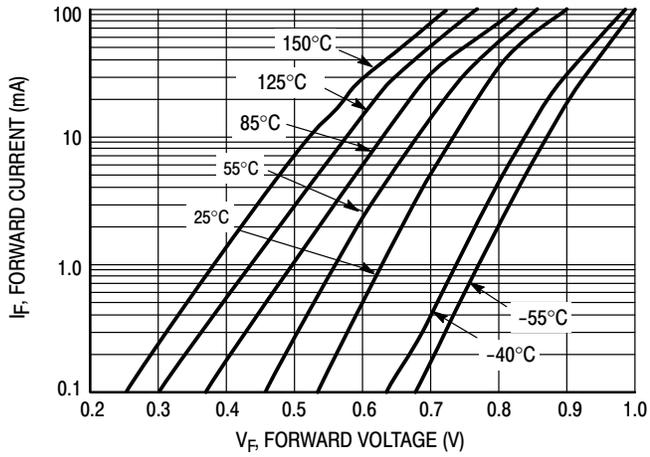**Figure 1. Recovery Time Equivalent Test Circuit**
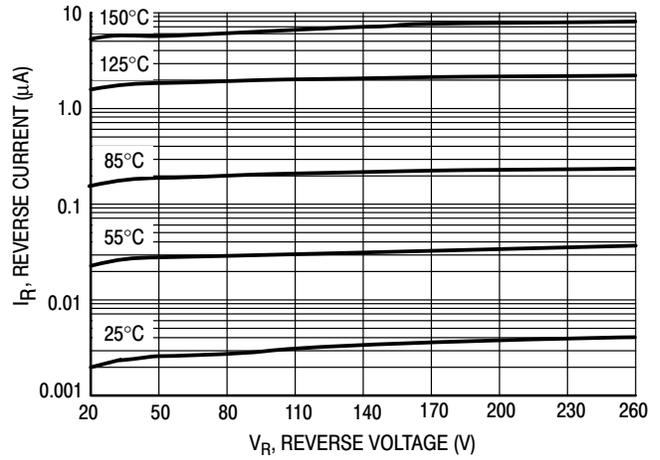
TYPICAL CHARACTERISTICS

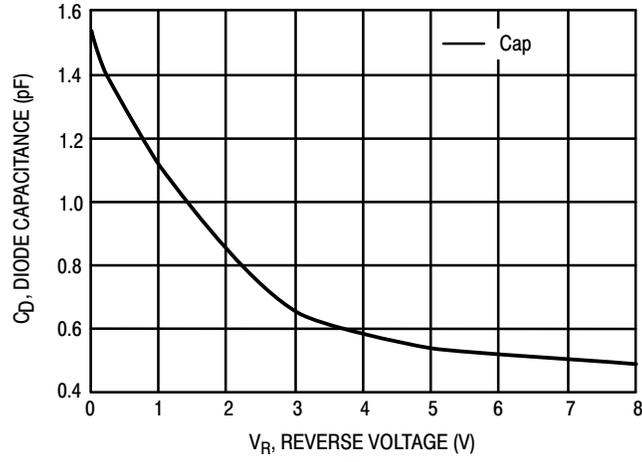**Figure 2. V_F vs. I_F**

Figure 3. I_R vs. V_R

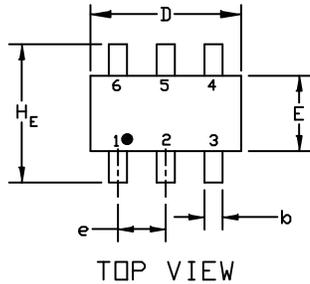**Figure 4. Capacitance**

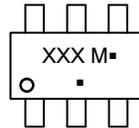**SC−74**
CASE 318F
ISSUE P

DATE 07 OCT 2021

6
1
SCALE 2:1

TOP VIEW

SIDE VIEW

0.05 (0.002)

END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994
2. CONTROLLING DIMENSION: INCHES
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
c	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
e	0.85	0.95	1.05	0.034	0.037	0.041
H_E	2.50	2.75	3.00	0.099	0.108	0.118
L	0.20	0.40	0.60	0.008	0.016	0.024
M	0°	---	10°	0°	---	10°

GENERIC
MARKING DIAGRAM*

XXX M■

XXX = Specific Device Code
M = Date Code
■ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

0.95 [0.037]   0.95 [0.037]

2.40 [0.094]

1.00 [0.039]

0.70 [0.028]
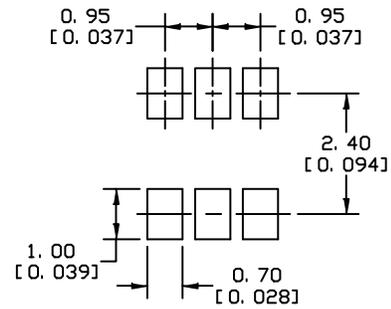
* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 2:
PIN 1. NO CONNECTION
2. COLLECTOR
3. EMITTER
4. NO CONNECTION
5. COLLECTOR
6. BASE

STYLE 3:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 4:
PIN 1. COLLECTOR 2
2. EMITTER 1/EMITTER 2
3. COLLECTOR 1
4. EMITTER 3
5. BASE 1/BASE 2/COLLECTOR 3
6. BASE 3

STYLE 5:
PIN 1. CHANNEL 1
2. ANODE
3. CHANNEL 2
4. CHANNEL 3
5. CATHODE
6. CHANNEL 4

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 8:
PIN 1. EMITTER 1
2. BASE 2
3. COLLECTOR 2
4. EMITTER 2
5. BASE 1
6. COLLECTOR 1

STYLE 9:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 10:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE

STYLE 11:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR

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DESCRIPTION:	SC−74		PAGE 1 OF 1

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